

We develop theoretical and computational methods to predict and engineer material and molecular properties from first principles.

### Overview



### Methods and Code Development

We develop methods based on quantum mechanics, and open-source software to understand and predict the properties of solids and molecules at the microscopic scale.

#### First Principles Molecular Dynamics (FPMD)

#### Many Body Perturbation Theory (MBPT)

M. Govoni and G. Galli, JCTC 2015, 2018; V. Yu et al. 2024 (submitted).

#### Time dependent DFT (TDDFT)

Y. Jin et al. JCTC 2023.

#### Quantum Embedding Theory (QDET)

M. He, M. Govoni, and G. Galli, npj Comput. Mater. 2020; N. Sheng, C. Vorwerk, M. Govoni, and G. Galli, JCTC 2022.

#### Cluster-Correlation Expansion (CCE)

M. Onizhuk and G. Galli 2024 (submitted).

#### Hybrid Density Functionals

J. Zhan, M. Govoni, and G. Galli JCTC 2023.

#### Path Integral Molecular Dynamics (PIMD)

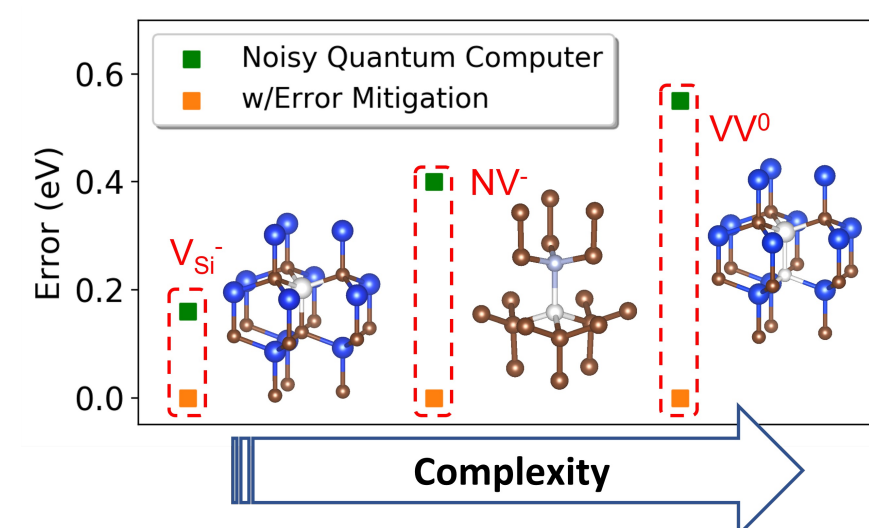
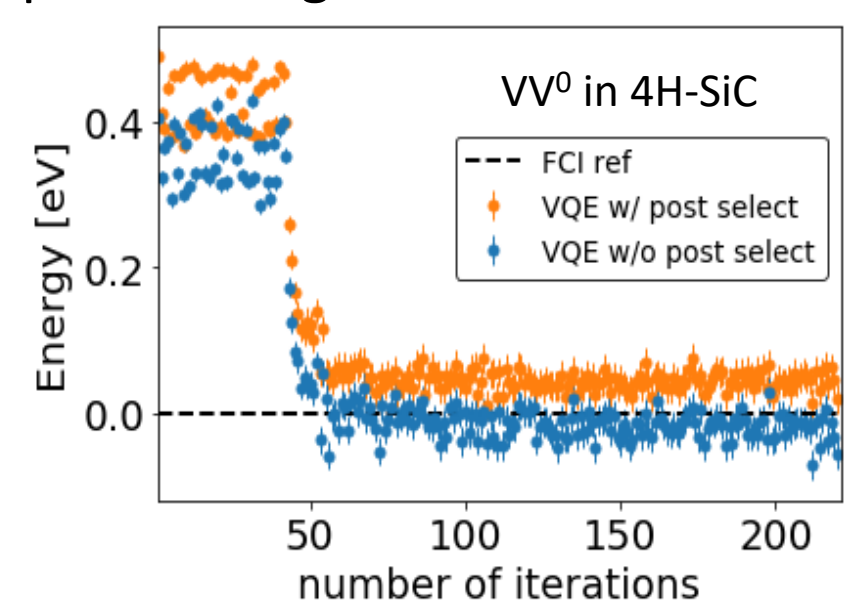
A. Kundu et al. Phys. Rev. Mater. Lett. 2021; PNAS 2022; JPCL 2024.



Codes are developed within the Midwest Integrated Center for Computational Materials: **MICCoM**

### Quantum Simulations on Quantum Computers

We use QDET to simulate the eigenstates of spin-defect systems with variational quantum eigensolver and shadow tomography-based algorithms.

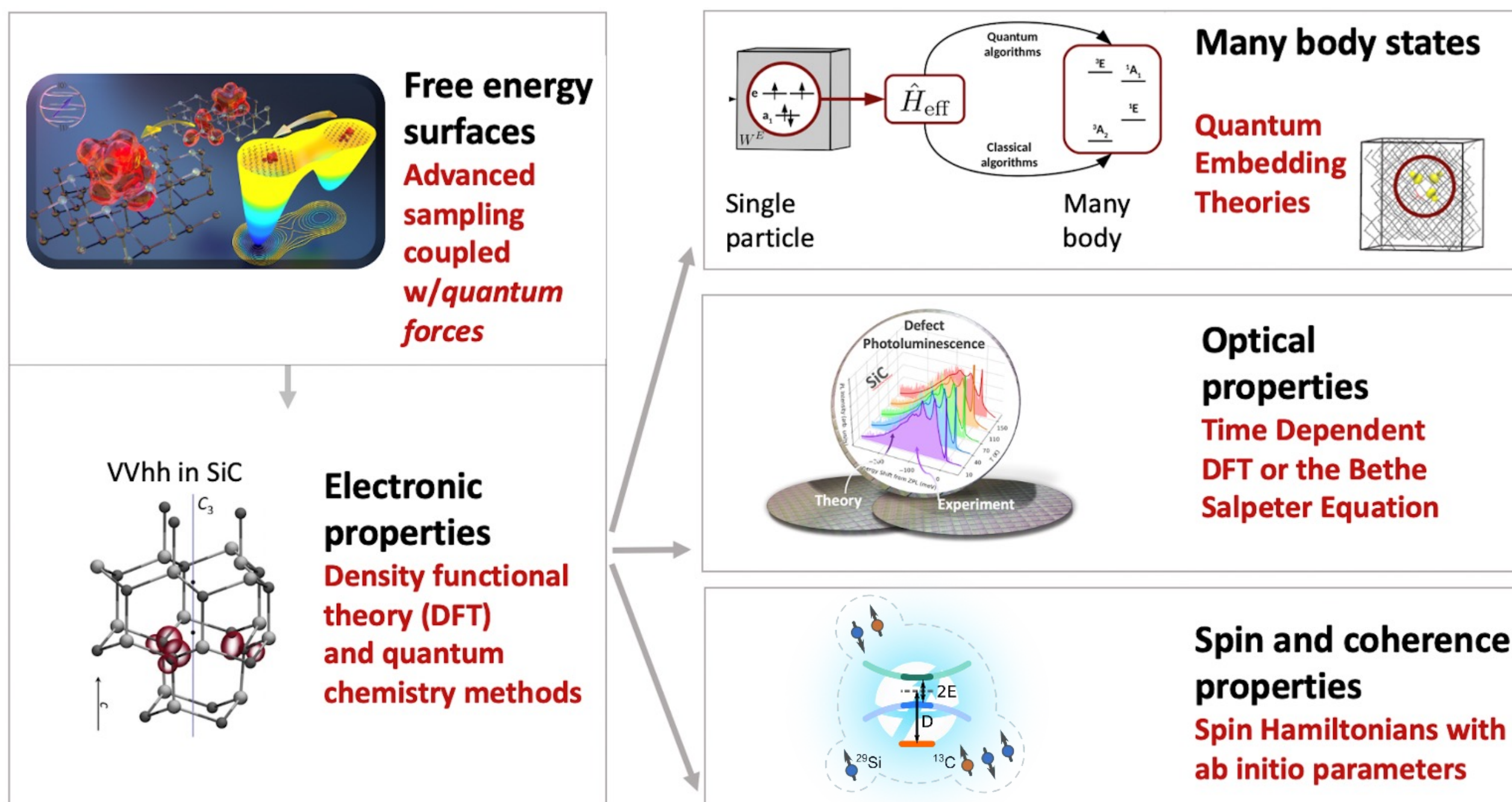


B. Huang, N. Sheng, M. Govoni, and G. Galli, JCTC 2023; B. Huang, M. Govoni, and G. Galli, PRX Quantum 2022; B. Huang et al. Phys. Rev. Research 2024.

We reduce the noise effects with the zero-noise extrapolation technique.

### Spin Qubits for Quantum Information Technologies

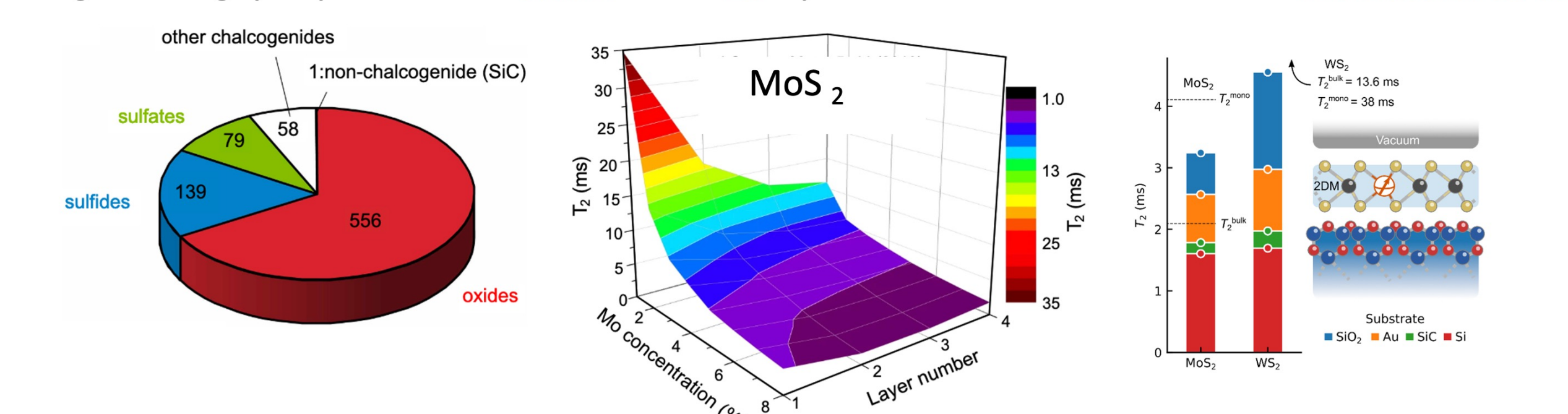
We aim to understand the atomic and electronic structure, and coherence properties of novel spin defects in semiconductors as platforms for quantum information processing.



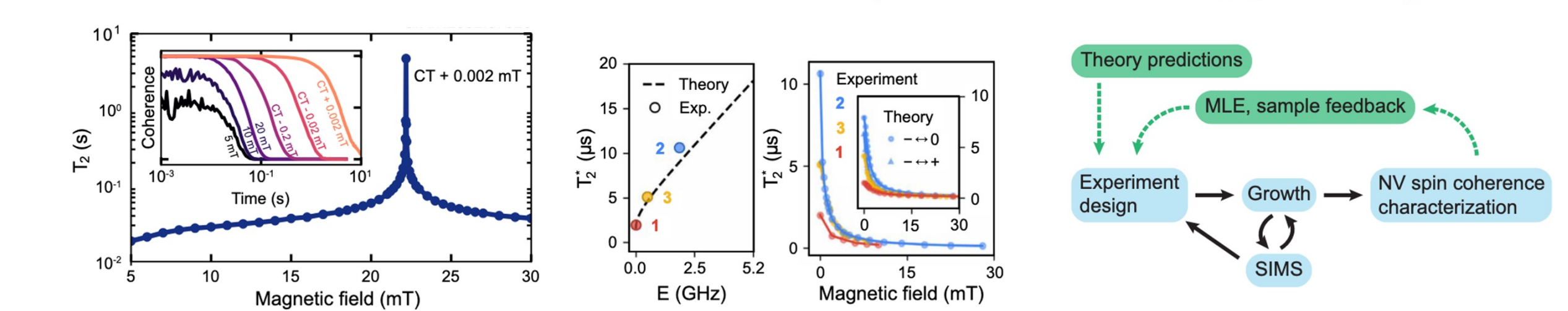
### Coherence Properties of Spin Qubits

We use CCE-based methods to understand decoherence dynamics in spin qubits:

High-throughput predictions: oxides, 2D Systems, van der Waals heterostructures



Clock transitions in oxides, Molecular qubits, Guiding growth experiments

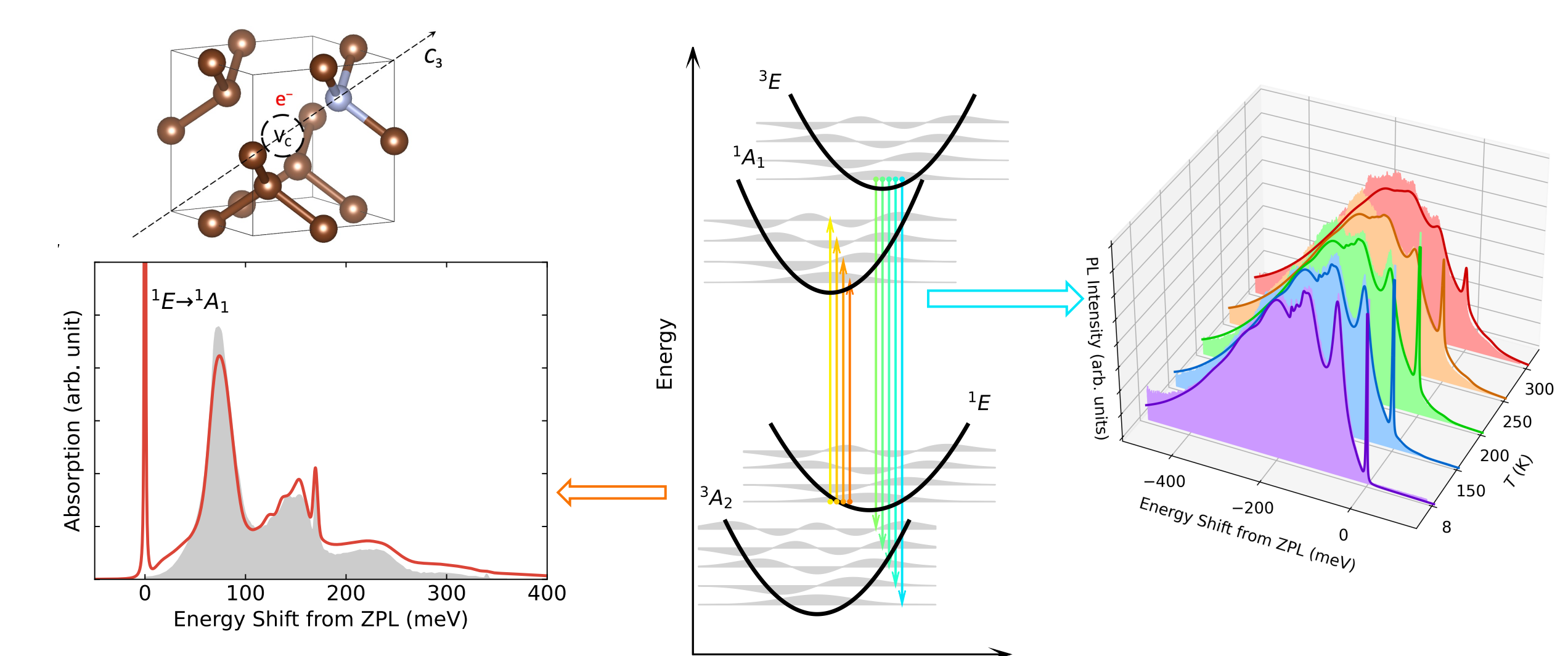


M. Onizhuk, Y.-X. Wang, J. Nagura, A. A. Clerk, and G. Galli, PRL 2024; M. Onizhuk and G. Galli, PRB 2023; J. C. Marcks\*, M. Onizhuk\*, N. Deegan, Y.-X. Wang, M. Fukami, M. Watts, A. A. Clerk, F. J. Heremans, G. Galli, and D. D. Awschalom, Phys. Rev. Mater. 2024; S. L. Bayliss, P. Deb, D. W. Laurenza, M. Onizhuk, G. Galli, D. E. Freedman, and D. D. Awschalom, PRX 2022; M. Onizhuk and G. Galli, Adv. Theory Simul. 2021; Y. Zhu, B. Kovos, M. Onizhuk, D. Awschalom, and G. Galli, Phys. Rev. Mater. 2021; M. Onizhuk and Giulia Galli, Appl. Phys. Lett. 2021; M. Onizhuk, K. C. Miao, J. P. Blanton, H. Ma, C. P. Anderson, A. Bourassa, D. D. Awschalom, and G. Galli, PRX Quantum 2021; A. Bourassa, C. P. Anderson, K. C. Miao, M. Onizhuk, H. Ma, A. L. Crook, H. Abe, J. Ul-Hassan, T. Ohshima, N. T. Son, G. Galli, and D. D. Awschalom, Nat. Mater. 2020.

### Computational Spectroscopy of Spin Defects

We develop *ab initio* approaches to compute optical spectra of point defects in semiconductors and insulators.

The TDDFT calculation of vibrationally resolved photoluminescence spectra, with excited state analytical forces, including spin-flip, is implemented in the WEST code.



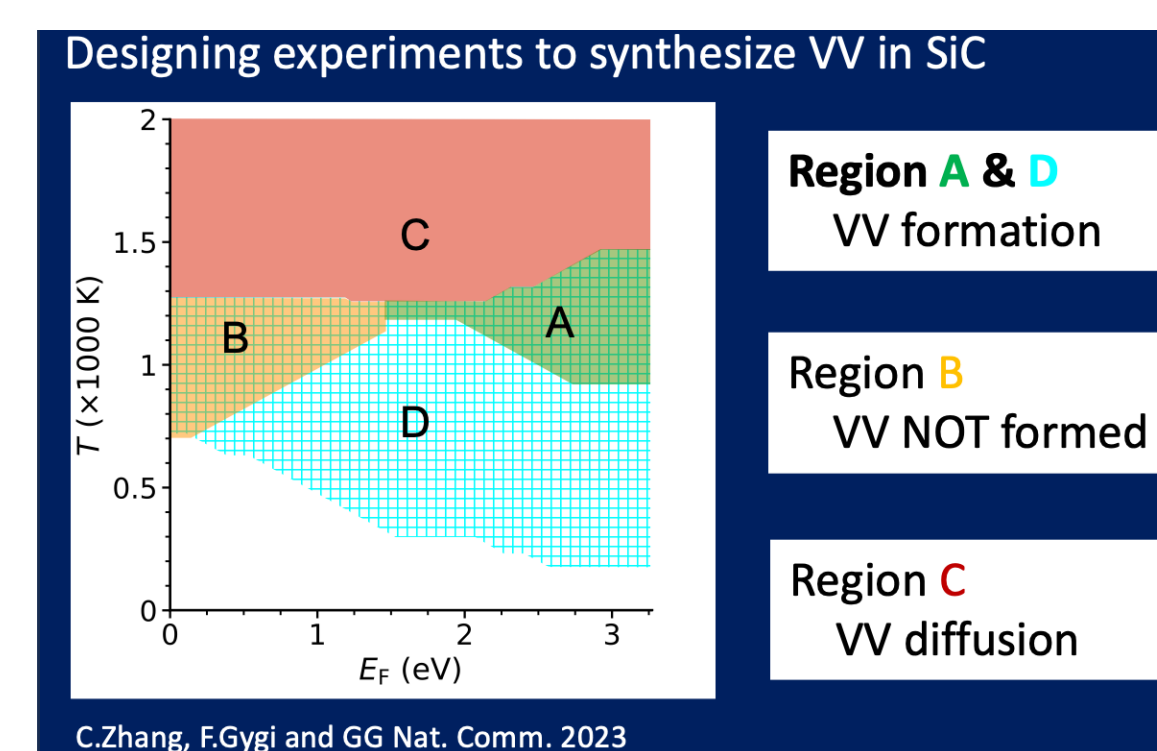
Yu Jin, Victor Wen-zhe Yu, Marco Govoni, Andrew C Xu, and Giulia Galli, JCTC 2023; Yu Jin, Marco Govoni, and Giulia Galli, npj Comput. Mater. 2022; C. P. Anderson\*, E. O. Glen\*, C. Zeledon, A. Bourassa, Y. Jin, Y. Zhu, C. Vorwerk, A. L. Crook, H. Abe, J. Ul-Hassan, T. Ohshima, N. T. Son, G. Galli, and D. D. Awschalom, Sci. Adv. 2022; Y. Zhu, B. Kovos, M. Onizhuk, D. Awschalom, and G. Galli, Phys. Rev. Mater. 2021; Y. Jin, M. Govoni, G. Wolfowicz, S. E. Sullivan, F. J. Heremans, D. D. Awschalom, and G. Galli, Phys. Rev. Mater. 2021.

### Formation of Spin Defects

We investigated the formation of a promising defect in SiC (double vacancy-VV) for quantum technology applications.

We combined first principles MD & advanced sampling.

We predicted the optimal annealing temperature and how to engineer the Fermi level to optimize the VV's yield in silicon carbide.



### Prediction of New Platforms

We search for new platforms by carrying out high-throughput searches and by exploring defect long range interactions, e.g., dipolar interaction between donor-acceptor pairs (DAPs).

